



- ☒ (0) ((float\$3 adj gate) same (control adj gate)) same (ald (at
- ☒ (31) ((float\$3 adj gate) same (control adj gate)) and (ald (at
- ☒ (76436) aluminum adj oxide
- ☒ (15399) ((barrier near (height tunnel)) ((energy diagram) ne
- ☒ (10315) work adj function
- ☒ (24895) (((barrier near (height tunnel)) ((energy diagram) ne
- ☒ (14) ((float\$3 adj gate) same (control adj gate)) same (alum
- ☒ (97) ((float\$3 adj gate) same (control adj gate)) same (((ba
- ☒ (0) (((float\$3 adj gate) same (control adj gate)) same (((ba
- ☒ (0) (((float\$3 adj gate) same (control adj gate)) same (((ba
- ☒ (173565) metal adj oxide
- ☒ (10) (((float\$3 adj gate) same (control adj gate)) same (((ba
- ☒ (387) ((float\$3 adj gate) same (control adj gate)) and (((ba
- ☒ (1) (((float\$3 adj gate) same (control adj gate)) and (((ba
- ☒ (31) ((float\$3 adj gate) same (control adj gate)) and (ald (at
- ☒ (9) (((barrier adj height) (energy adj band))) near2 (asymme
- ☒ (41) (((float\$3 adj gate) same (control adj gate)) same (((ba
- ☒ (49) (((barrier adj height) (energy adj band))) near2 (asymme

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Default operator: OR

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(((barrier adj height) (energy adj band))) near2 (asymmetr\$4 differ\$2) and (float\$3 adj gate) and (control adj gate) (((float\$3 adj gate) same (control adj gate)) same (((barrier near (height tunnel)) (energy diagram) near band)) (work adj function))) and (metal adj oxide) (((float\$3 adj gate) same (control adj gate)) and (ald (atomic adj layer adj deposit\$3)))

Dec 2002

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	U	Inventor	Document ID	Issue Date	Page	Title	Current OR	Current XRef	Ret
1	<input checked="" type="checkbox"/>	Faraone, Lorenzo	US 4757360 A	19880712	6	Floating gate memory device with facing asperities on floating and control gates	257/317	257/900; 257/E29.304	
2	<input type="checkbox"/>	Kan, Edwin C. et al.	US 20020192949 A1	20021219	14	Embedded metal nanocrystals	438/652	438/660	
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5	<input checked="" type="checkbox"/>	Lee, Woo-Hyeong et al.	US 5923056 A	19990713	6	Electronic components with doped metal oxide dielectric materials and a process for making electronic components with doped metal oxide	257/192	257/410; 257/411	
6	<input checked="" type="checkbox"/>	Muralidhar, Ramachandran et al.	US 6320784 B1	20011120	7	Memory cell and method for programming thereof	365/151	257/E29.301; 257/E29.308	
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8	<input checked="" type="checkbox"/>	Uchida, Hidetsugu	US 6229175 B1	20010508	24	Nonvolatile memory	257/315	257/298; 257/316	